METHOD FOR EVALUATION OF BONDED WAFER

ABSTRACT OF THE DISCLOSURE

A bonded wafer formed by directly bonding a wafer for active layer and a wafer for support substrate without an insulating film and thinning the wafer for active layer is evaluated by a method comprising steps of removing native oxide from a surface of an active layer in the bonded wafer, subjecting the bonded wafer to an etching with an etching liquid having an etching rate to a material constituting the wafer faster than that to an oxide of the material to remove at least a whole of the active layer, and detecting island-shaped oxides exposed by the etching, in which the etching is carried out so as to satisfy a relation of $T \leq X \leq T+500$ nm wherein T is a thickness of the active layer (nm) and X is an etching depth (nm) to detect the number and size of the island-shaped oxides.

Fig. 1